"Yت / Descriptions

SOP-8 P MOS

Double P-CHANNEL MOSFET in a SOP-8 Plastic Package.

◕È / Features

V_{DS}=-60V; I_D=-3.5A

$R_{DS(on)1}$@-10V ≤ 100mΩ(Type.83mΩ)

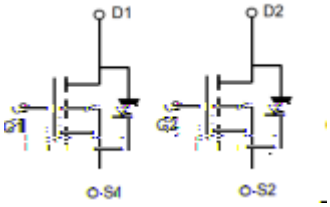
$R_{DS(on)2}$@-4.5V ≤ 130mΩ(Type.100mΩ)

AEC-Q101 Qualified to AEC-Q101 Standards for High Reliability, HF Product.

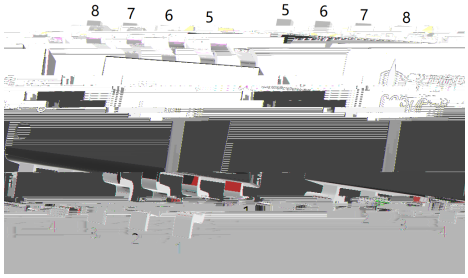
٭ ږ / Applications

Power Management in Computer, Portable Equipment and Battery Powered Systems,Load Switches,Motor Control, Meet the stringent requirements of automotive applications.

Лق ٚ ≠ ع / Equivalent Circuit



ãﺃ ٶ / Pinning



PIN1 S1 PIN 2 G1 PIN 3 S2 PIN 4 G2

PIN 5 D2 PIN 6 D2 PIN 7 D1 PIN 8 D1

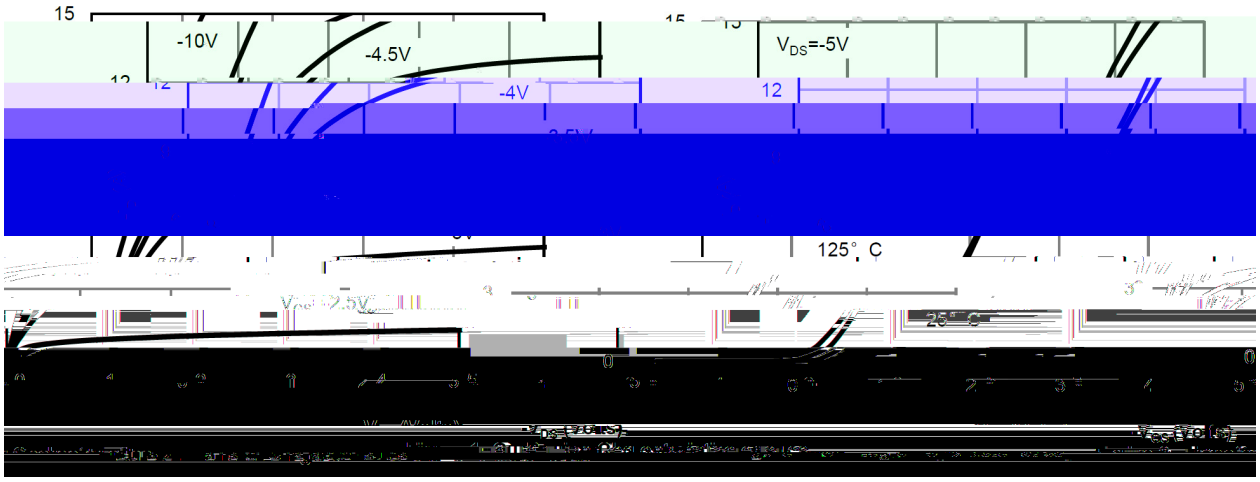
ł. ʜ ڍ / Marking

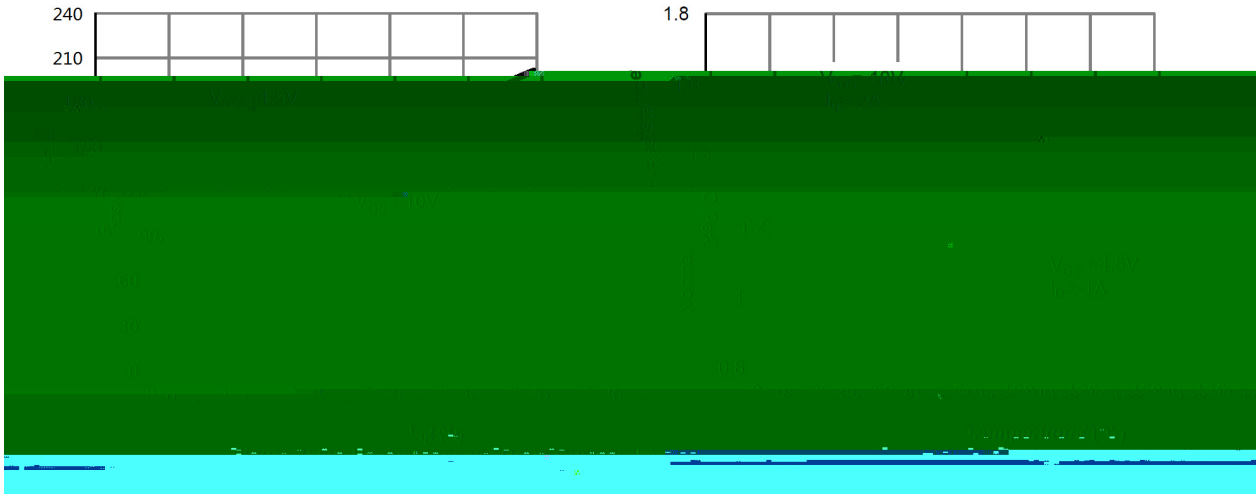
See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain–Source Voltage		V_{DSS}	-60	V
Gate–Body Leakage Voltage		V_{GSS}	±20	V
Drain Current – Continuous		I_D	-3.5	A
Pulsed Drain Current		I_{DM}	-16	A
Power Dissipation		P_D	2	W
Operating and Storage Temperature Range		T_J,T_{STG}	-55 150	
Maximum Junction-to-Ambient	Steady-State	$R_{\theta JA}$	62.5	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V I_D=-250μ				

⁄ ∃ ˜Ą´E ¼ ƒ / Electrical Characteristic Curve





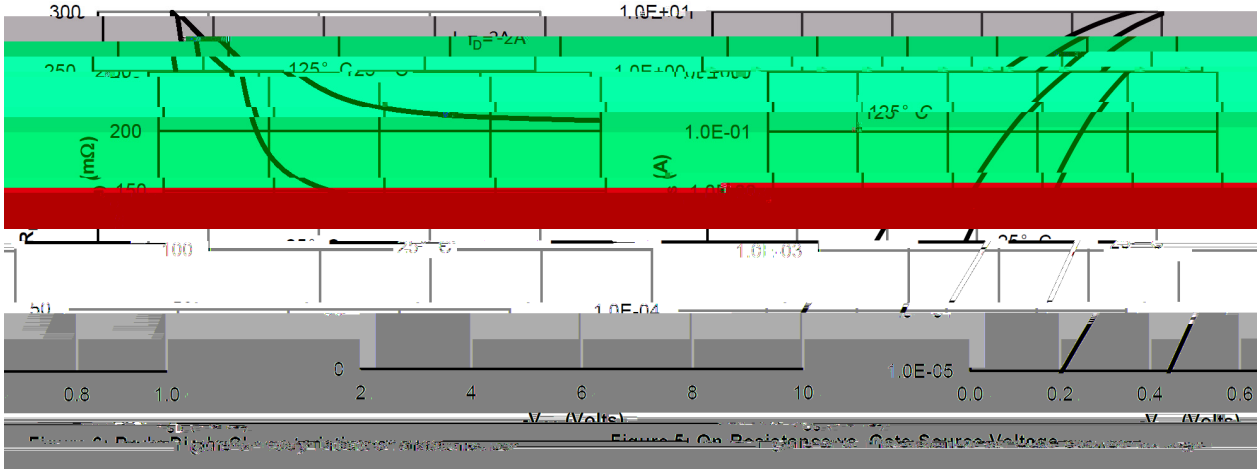


Figure 5: On-Resistance vs. Gate-Source Voltage

≠ ∃ Ã´E ∀ ƒ / Electrical Characteristic Curve

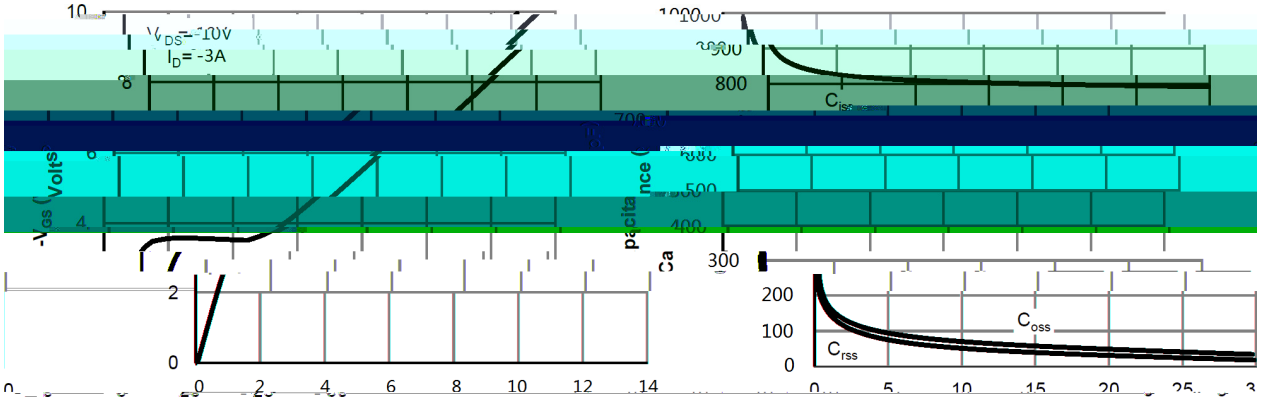
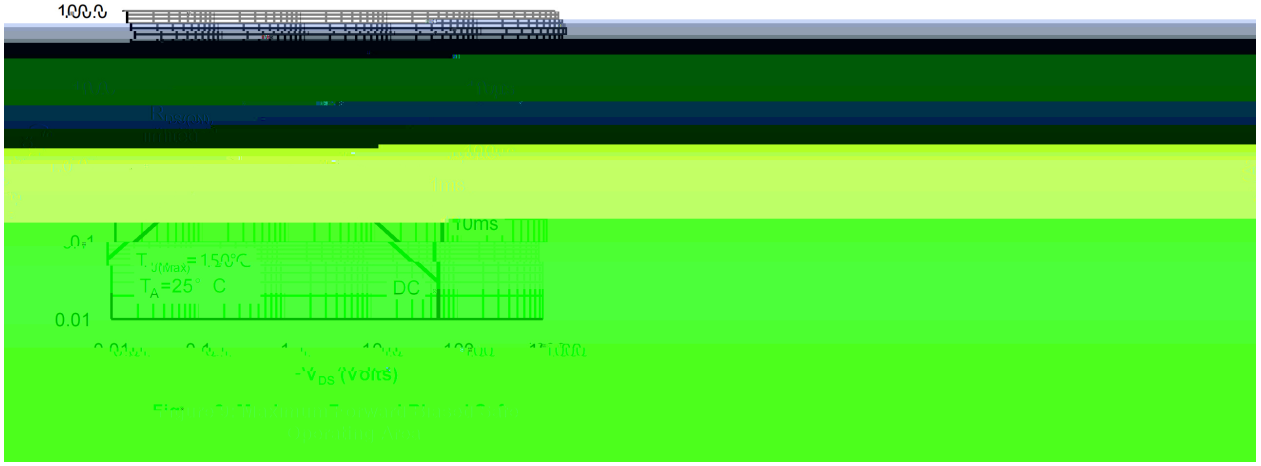
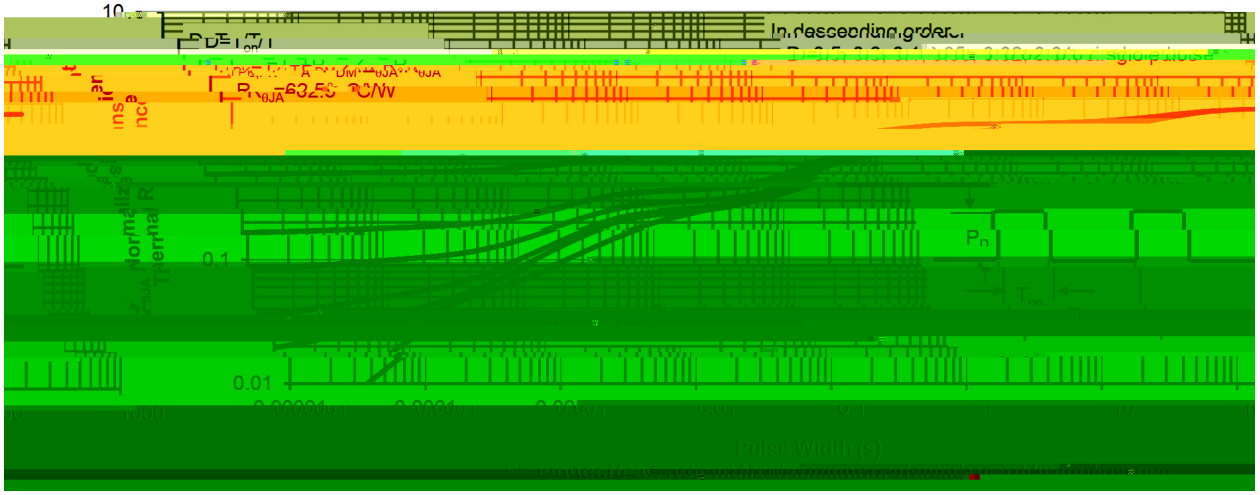
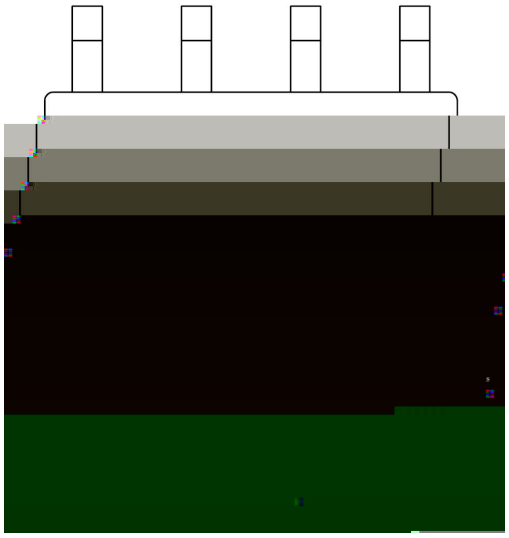


Figure 7: Gate-Charge Characteristics





ł. Ļ Ω / Marking Instructions



0BRfT*.0004 Tc1.090 Tw(6)Tj<1 Tf3.0012 0 TD1aa07a2c.22511373(e)22 1726.4(Tf-3.497 0 TD